

Silicon N Channel Power MOSFET

Description

The HXN10B0 is n-channel power trench MOSFET with latest technology. So fast switching speed and low on-resistance. Usually used at power switching application . It is also intended for any applications with low gate drive requirements .

Features

- Latest Trench Power MOSFET technology
- Low On-state Resistance
- High Current Density
- Low Gate Charge
- 100% UIS Test

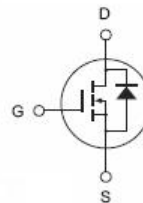
Product Summary

BVDS	RDSON	ID
100V	10mΩ	100A

Applications

- Motor Driver
- Power Management

TO-220 Package



1、 Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{GS}	Gate-source voltage	±25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	100	A
$I_{DM}^{(2)}$	Drain current (pulsed)	350	A

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P_D	Power dissipation at $T_C = 25\text{ }^\circ\text{C}$	250	W
$E_{AS}^{(3)}$	Single pulse avalanche energy	1000	mJ
T_j	Operating junction temperature	-55 to 150	$^\circ\text{C}$

1. Current limited by package
2. Pulse width limited by safe operating area
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 46\text{A}$, $V_{DD} = 30\text{V}$, $L = 1\text{mH}$

2、 Thermal data

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		62.5		$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case		0.5		$^\circ\text{C}/\text{W}$

3、 Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain	$V_{DS} = \text{Max rating}$			1	μA
I_{GSS}	Gate body leakage current	$V_{GS} = \pm 25\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$	2	2.8	4	V
$R_{DS(on)}$	Static drain-source on	$V_{GS} = 10\text{V}$		8	10	m Ω
C_{iss}	Input capacitance	$V_{DS} = 25\text{V}$		5200		pF
C_{oss}	Output capacitance	$f = 1\text{ MHz}$		370		pF
C_{rss}	Reverse transfer	$V_{GS} = 0$		240		pF
Q_g	Total gate charge	$V_{DD} = 30\text{V}$		124		nC
Q_{gs}	Gate-source charge	$I_D = 40\text{A}$		34		nC
Q_{gd}	Gate-drain charge	$V_{GS} = 10\text{V}$		25		nC
I_{SD}	Source-drain current				100	A

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$I_{SDM}^{(1)}$	Source-drain current (pulsed)				350	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 98A, V_{GS} = 0$			1.2	V

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μ s, duty cycle 1.5%